

IN THE CLAIMS

Please amend the Claims as follows:

1 (Currently Amended). A semiconductor stacking structure comprising:

a first semiconductor device; and

a flexible tape substrate having metal layers for electrical connections wherein the flexible tape substrate is coupled to a bottom surface of the first semiconductor device via the metal layers, wherein the flexible substrate is being folded over on at least two sides ~~so as to not overlap~~ and to form flap portions which are coupled to an upper surface of the first semiconductor device, and wherein the flap portions not over lapping one another and covering only a portion section of the upper surface of the first semiconductor device which is smaller than the upper surface of the first semiconductor device, the flexible substrate used for stacking additional semiconductor devices on the flap portions wherein the additional semiconductor devices are coupled to the metal layers of the flexible substrate; and ~~first semiconductor device.~~

2 (Original). A semiconductor stacking structure in accordance with Claim 1 further comprising an adhesive layer which is placed on the flap portions of the flexible substrate and which couples the flap portions to the first semiconductor device.

3 (Original). A semiconductor package in accordance with Claim 1 further comprising an adhesive layer which is placed on the upper surface of the first semiconductor device and which couples the flap portions to the first semiconductor device.

4 (Original). A semiconductor stacking structure in accordance with Claim 1 further comprising a second semiconductor device coupled to the flap portions of the flexible substrate.

5 (Original). A semiconductor stacking structure in accordance with Claim 4 wherein the second semiconductor device is coupled to the flap portions of the flexible substrate after the flap portions are folded over and coupled to the first semiconductor device.

6 (Original). A semiconductor stacking structure in accordance with Claim 4 wherein the second semiconductor device is coupled to the flap portions of the flexible substrate before the flap portions are folded over and coupled to the first semiconductor device.

7 (Original). A semiconductor stacking structure package in accordance with Claim 1 wherein the semiconductor stacking structure is a LGA (Land Grid Array) device.

8 (Original). A semiconductor stacking structure in accordance with Claim 1 wherein the semiconductor stacking structure is a BGA (Ball Grid Array) device.

9 (Original). A semiconductor stacking structure in accordance with Claim 1 wherein the semiconductor stacking structure is a lead type of device.

10 (Original). A semiconductor stacking structure in accordance with Claim 1 wherein the flexible substrate is folded over on four sides to form flap portions which are coupled to the upper surface of the first semiconductor device and covers only a portion of the upper surface of the first semiconductor device.

11 (Currently Amended). A semiconductor stacking structure comprising:

a first semiconductor device; and
means having metal layers for electrical connections coupled to a bottom surface of the first semiconductor device via the metal layers for forming the semiconductor stacking structure, wherein the means is folded over on at least two sides so as to not overlap and coupled to an upper surface of the first semiconductor device and covers only a portion of the upper surface of the first semiconductor device which is smaller than the upper surface of the first semiconductor device, the flexible substrate used for stacking additional semiconductor devices on folded over portions of the means, the additional semiconductor devices coupled to the metal layers of the means the first semiconductor device.

12 (Original). A semiconductor stacking structure in accordance with Claim 11 further comprising an adhesive layer placed on the means for coupling the means to the upper surface of the first semiconductor device.

13 (Cancelled). A method of forming a semiconductor structure comprising:

providing a flexible substrate;

forming a first semiconductor device on the flexible substrate;

folding over on at least two sides the flexible substrate; and

coupling to an upper surface of the first semiconductor device the flexible substrate which is folded to form flap portions wherein the flap portions of the flexible substrate will cover only a portion of the upper surface of the first semiconductor device.

14 (Cancelled). The method of Claim 13 further comprising applying an adhesive layer on the flap portions of the flexible substrate for coupling the flap portions of the flexible substrate to the first semiconductor device.

15 (Cancelled). The method of Claim 13 further comprising applying an adhesive layer to the upper surface of the semiconductor device for coupling the flap portions of the flexible substrate to the first semiconductor device.

16 (Cancelled). The method of Claim 13 further comprising:

providing a second semiconductor device; and
coupling the second semiconductor device to the flap portions of the flexible substrate after the flap portions are coupled to the upper surface of the first semiconductor device.

17 (Cancelled). The method of Claim 13 further comprising:

providing a second semiconductor device; and
coupling the semiconductor device to the flap portions of the flexible substrate before the flap portions are coupled to the upper surface of the first semiconductor device.

18 (Cancelled). The method of Claim 13 further comprising forming contacts on the flexible substrate.

19 (Cancelled). The method of Claim 13 wherein folding over on at least two sides the flexible substrate further comprises folding over the flexible substrate on four sides.

20 (Cancelled). The method of Claim 19 further comprising the cutting adjoining flap portions to narrow a size of the adjoining flap portions so the flap portions will not overlap or contact each other.

21 (Currently Amended). A semiconductor stacking structure comprising:

a first semiconductor device; and

means a flexible tape substrate having metal layers on a top and bottom surface for electrical connections, the flexible tape substrate coupled to a bottom surface of the first semiconductor device via the metal layers for forming the semiconductor stacking structure wherein the means is folded over on ~~at least two~~ four sides so as to not overlap to form flap portions which are coupled to an upper surface of the first semiconductor device and covers only a portion of the upper surface of the first semiconductor device which is smaller than the upper surface of the first semiconductor device, the flap portions increasing connect density of the semiconductor stacking structure and used for stacking additional semiconductor devices on the first semiconductor, the additional semiconductor devices coupled to the metal layers of the means.

22 (Original). A semiconductor stacking structure in accordance with Claim 21 further comprising means placed on the flap portions of the flexible substrate for coupling the flap portions to the first semiconductor device.

23 (Original). A semiconductor package in accordance with Claim 21 further comprising means placed on the upper surface of the first semiconductor device for coupling the flap portions to the first semiconductor device.

24 (Original). A semiconductor stacking structure in accordance with Claim 21 further comprising a second semiconductor device coupled to the flap portions of the ~~means~~ flexible tape substrate.

25 (Original). A semiconductor stacking structure in accordance with Claim 24 wherein the second semiconductor device is coupled to the flap portions of the ~~means~~ flexible tape substrate after the flap portions are folded over and coupled to the first semiconductor device.

26 (Original). A semiconductor stacking structure in accordance with Claim 24 wherein the second semiconductor device is coupled to the flap portions of the ~~means~~ flexible tape substrate before the flap portions are folded over and coupled to the first semiconductor device.

27 (Original). A semiconductor stacking structure package in accordance with Claim 21 wherein the semiconductor stacking structure is a LGA (Land Grid Array) device.

28 (Original). A semiconductor stacking structure in accordance with Claim 21 wherein the semiconductor stacking structure is a BGA (Ball Grid Array) device.